

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	3822692	(open\$3 groove recess)	US-PGPU B; USPAT; USOCR	OR	ON	2005/02/22 09:18
L2	155130	1 and mask	US-PGPU B; USPAT; USOCR	OR	ON	2005/02/22 09:19
L3	3935422	(open\$3 groove recess cavity)	US-PGPU B; USPAT; USOCR	OR	ON	2005/02/22 07:31
L4	404121	3 and (oxide nitride)	US-PGPU B; USPAT; USOCR	OR	ON	2005/02/22 09:19
L5	14085	4 and (pad near5 layer)	US-PGPU B; USPAT; USOCR	OR	ON	2005/02/22 07:34
L6	14085	5 and (pad near5 layer)	US-PGPU B; USPAT; USOCR	OR	ON	2005/02/22 07:35
L7	3040	6 and (thermal\$3 near5 (oxid\$3 Oxidizing))	US-PGPU B; USPAT; USOCR	OR	ON	2005/02/22 09:19
L8	1607	7 and (spacer liner)	US-PGPU B; USPAT; USOCR	OR	ON	2005/02/22 07:39
L9	1583	8 and (semiconductor wafer)	US-PGPU B; USPAT; USOCR	OR	ON	2005/02/22 08:16
L10	96	9 and SIMOX	US-PGPU B; USPAT; USOCR	OR	ON	2005/02/22 08:14
L11	1337	9 and oxidation	US-PGPU B; USPAT; USOCR	OR	ON	2005/02/22 08:30
L12	0	(RIE near5 isotropic near5 etch\$3) same (flourine near5 gas)	US-PGPU B; USPAT; USOCR	OR	ON	2005/02/22 08:31
L13	146530	(RIE (reactive near5 etch\$3))	US-PGPU B; USPAT; USOCR	OR	ON	2005/02/22 08:33
L14	6317	13 and isotropic	US-PGPU B; USPAT; USOCR	OR	ON	2005/02/22 08:33
L16	1252	14 and (fluorine ("N" adj3 "F.sub.3") ("S" adj3 "F.sub.6") ("C" adj3 "F.sub.4"))	US-PGPU B; USPAT; USOCR	OR	ON	2005/02/22 08:35

L17	324	16 and (thermal\$3 near5 (oxid\$3 Oxidizing))	US-PGPU B; USPAT; USOCR	OR	ON	2005/02/22 08:36
L18	2714540	(open\$3 groove recess)	EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/02/22 09:18
L19	32441	18 and mask	EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/02/22 09:19
L20	0	19 and (oxide nitride)	US-PGPU B; USPAT; USOCR	OR	ON	2005/02/22 09:19
L21	7204	19 and (oxide nitride)	EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/02/22 09:19
L22	796	21 and (thermal\$3 near5 (oxid\$3 Oxidizing))	EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/02/22 09:20